

MOSFETs Silicon P-Channel MOS

# SSM3J35AFS

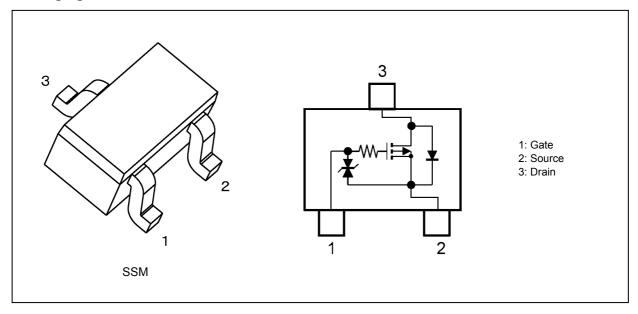
### 1. Applications

· Analog Switches

#### 2. Features

- (1) 1.2 V drive
- (2) ESD(HBM) level 2 kV
- (3) Low drain-source on-resistance
  - :  $R_{DS(ON)} = 3.2 \Omega$  (typ.) (@ $V_{GS} = -1.2 \text{ V}$ )
  - $R_{\rm DS(ON)} = 2.3~\Omega~{\rm (typ.)}~(@V_{\rm GS} = -1.5~{\rm V})$
  - $R_{DS(ON)} = 2.0 \Omega \text{ (typ.) } (@V_{GS} = -1.8 \text{ V})$
  - $\rm R_{DS(ON)} = 1.5~\Omega$  (typ.) (@V\_{GS} = -2.5~V)
  - $R_{\rm DS(ON)}=1.1~\Omega$  (typ.) (@V<sub>GS</sub> = -4.5 V)

### 3. Packaging and Internal Circuit





### 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 °C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V <sub>DSS</sub>	-20	V
Gate-source voltage		$V_{GSS}$	±10	
Drain current (DC)	(Note 1)	I <sub>D</sub>	-250	mA
Drain current (pulsed)	(Note 1)	I <sub>DP</sub>	-600	
Power dissipation	(Note 2)	$P_{D}$	150	mW
Power dissipation	(Note 3)		500	
Channel temperature		T <sub>ch</sub>	150	°C
Storage temperature		T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150 °C.
- Note 2: Mounted on an FR4 board (25.4 mm  $\times$  25.4 mm  $\times$  1.6 mm, Cu pad: 0.36 mm<sup>2</sup>  $\times$  3)
- Note 3: Mounted on an FR4 board (25.4 mm × 25.4 mm × 1.6 mm, Cu pad: 645 mm<sup>2</sup>)
- Note: This transistor is sensitive to electrostatic discharge and should be handled with care.
- Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.
- Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.



#### 5. Electrical Characteristics

### 5.1. Static Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}$	_	_	±1	μА
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = -20 V, V <sub>GS</sub> = 0 V	_	_	-1	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 0 V	-20	_	_	V
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 10 V	-10	_	_	
Gate threshold voltage	(Note 2)	$V_{th}$	$V_{DS}$ = -10 V, $I_{D}$ = -100 $\mu$ A	-0.3	_	-1	
Drain-source on-resistance	(Note 3)	R <sub>DS(ON)</sub>	$I_D$ = -10 mA, $V_{GS}$ = -1.2 V	_	3.2	20	Ω
			I <sub>D</sub> = -20 mA, V <sub>GS</sub> = -1.5 V	_	2.3	4.0	
			$I_D = -50 \text{ mA}, V_{GS} = -1.8 \text{ V}$	_	2.0	2.9	
			I <sub>D</sub> = -150 mA, V <sub>GS</sub> = -2.5 V	_	1.5	2.1	
			I <sub>D</sub> = -150 mA, V <sub>GS</sub> = -4.5 V	_	1.1	1.4	
Forward transfer admittance	(Note 3)	Y <sub>fs</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -100 mA	_	430	_	mS

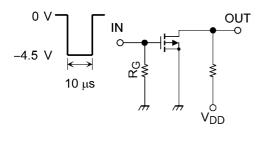
- Note 1: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.
- Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current ( $I_D$ ) to below (-100  $\mu$ A for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ . Take this into consideration when using the device.

Note 3: Pulse measurement.

# 5.2. Dynamic Characteristics (Unless otherwise specified, $T_a = 25$ °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V,	_	21	42	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	2	_	
Output capacitance	C <sub>oss</sub>		_	6	_	
Switching time (rise time)	t <sub>r</sub>	V <sub>DD</sub> = -10 V, I <sub>D</sub> = -50 mA,	_	42	_	ns
Switching time (turn-on delay time)	t <sub>d(on)</sub>	$V_{GS}$ = 0 to -4.5 V, $R_{G}$ = 10 Ω Duty ≤ 1%, $V_{IN}$ : $t_{r}$ , $t_{f}$ < 5 ns,	_	17	_	
Switching time (fall time)	t <sub>f</sub>	Common source, See Chapter 5.3.	_	145	_	
Switching time (turn-off delay time)	t <sub>d(off)</sub>	]	_	420	_	

### 5.3. Switching Time Test Circuit



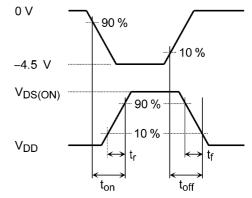


Fig. 5.3.1 Switching Time Test Circuit

Fig. 5.3.2 Input Waveform/Output Waveform

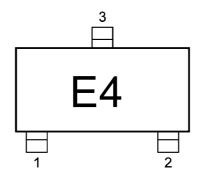


# 5.4. Source-Drain Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

	Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
D	iode forward voltage	(Note 1)	$V_{DSF}$	I <sub>D</sub> = 100 mA, V <sub>GS</sub> = 0 V	_	0.83	1.2	V

Note 1: Pulse measurement.

# 6. Marking



### 7. Characteristics Curves (Note)

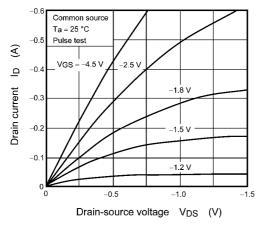
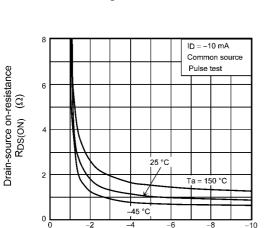


Fig. 7.1 I<sub>D</sub> - V<sub>DS</sub>



Gate-source voltage V<sub>GS</sub> (V) Fig. 7.3 R<sub>DS(ON)</sub> - V<sub>GS</sub>

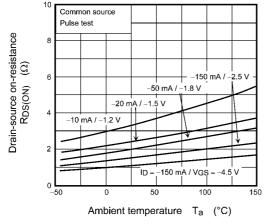


Fig. 7.5 R<sub>DS(ON)</sub> - T<sub>a</sub>

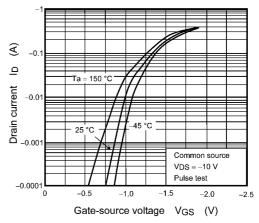


Fig. 7.2 I<sub>D</sub> - V<sub>GS</sub>

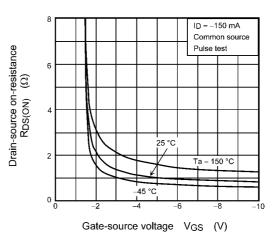


Fig. 7.4 R<sub>DS(ON)</sub> - V<sub>GS</sub>

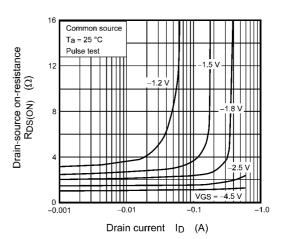


Fig. 7.6 R<sub>DS(ON)</sub> - I<sub>D</sub>

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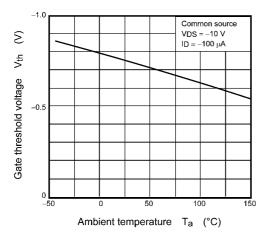


Fig. 7.7 Vth - Ta

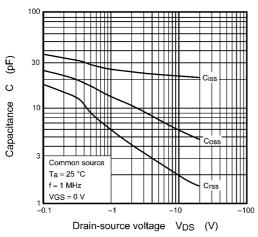
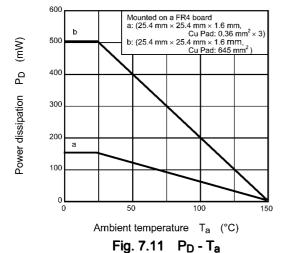


Fig. 7.9 C - V<sub>DS</sub>



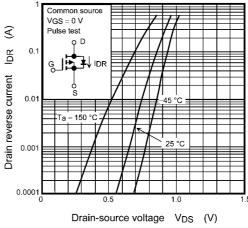


Fig. 7.8 IDR - VDS

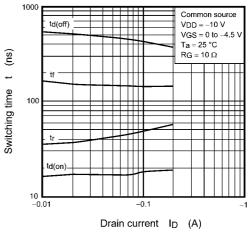


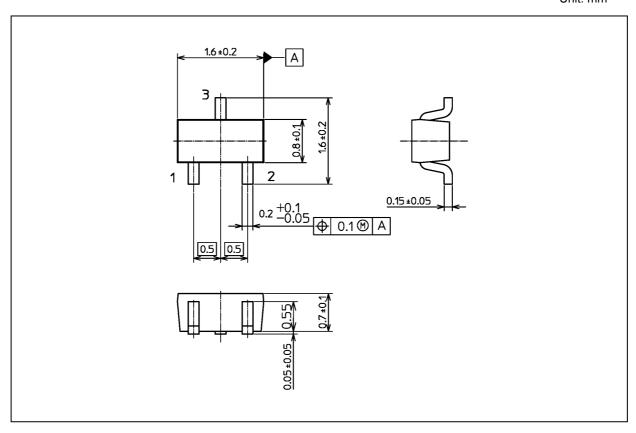
Fig. 7.10 t - I<sub>D</sub>

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



# **Package Dimensions**

Unit: mm



Weight: 2.4 mg (typ.)

	Package Name(s)
JEDEC: SOT-416	
Nickname: SSM	

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